

**DESCRIPTION**

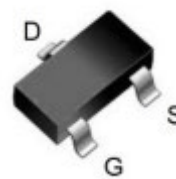
The AM2301C is available in SC70-3 Package.

FEATURE

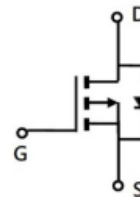
- TrenchFET Power MOSF
- Available in SC70-3 Package

APPLICATION

- Load Switch for Portable Devices
- DC/DC Converter

PIN DESCRIPTION

SC70-3

**ORDERING INFORMATION**

Package Type	Part Number	
SC70-3	C3	AM2301CC3VR
SPQ: 3,000pcs/Reel		AM2301CC3VR
Note	R: Tape & Reel V: Halogen free Package	
AiT provides all RoHS products		

Pin#	Symbol	Function
1	G	Gate
2	S	Source
3	D	Drain

ABSOLUTE MAXIMUM RATINGS

T_A=25°C, unless otherwise noted.

V _{DS} , Drain-Source Voltage	-20V
V _{GS} , Gate-Source Voltage	±8V
I _D , Continuous Drain Current	-3A
I _{DM} , Pulsed Drain Current	-10A
I _S , Continuous Source-Drain Diode Current	-0.72A
P _D , Maximum Power Dissipation	0.35W
R _{θJA} , Thermal Resistance from Junction to Ambient (t ≤5s)	357mJ
T _{STG} , Storage Temperature	-55°C~+150°C
T _J , Junction Temperature	150°C

Stresses above may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated in the Electrical Characteristics are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



ELECTRICAL CHARACTERISTICS

T_A=25°C, unless otherwise noted.

Parameter	Symbol	Conditions	Min	Typ.	Max	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =-250μA	-20	-	-	V
Gate-Source Threshold Voltage	V _{GS(TH)}	V _{GS} =V _{DS} , I _D =-250uA	-0.40	-	-1	V
Gate-Source Leakage	I _{GSS}	V _{GS} =±8V, V _{DS} =0V	-	-	±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-16V, V _{GS} =0V	-	-	-1	μA
Drain-Source On-State Resistance (1)	R _{DS(ON)}	V _{GS} =-4.5V, I _D =-3A	-	0.09	0.11	mΩ
		V _{GS} =-2.5V, I _D =-2A	-	0.11	0.14	
Forward Transconductance (1)	g _{FS}	V _{DS} =-5V, I _D =-2.8A	-	6.50	-	S
Dynamic (2)						
Input Capacitance	C _{iss}	V _{DS} =-10V, V _{GS} =0V, f=1MHz	-	405	-	pF
Output Capacitance	C _{oss}		-	75	-	
Reverse Transfer Capacitance	C _{rss}		-	55	-	
Total Gate Charge	Q _g	V _{DS} =-10V, I _D =-3A, V _{GS} =-4.5V	-	5.5	10	nC
		V _{DS} =-10V, I _D =-3A, V _{GS} =-2.5V	-	3.3	6	
Gate-Source Charge	Q _{gs}	V _{DS} =-10V, I _D =-3A, V _{GS} =-2.5V	-	0.7	-	
Gate-Drain Charge	Q _{gd}		-	1.3	-	
Gate Resistance	R _g	f=1MHz	-	6	-	Ω
Turn-on Delay Time	t _{d(on)}	V _{DD} =-10V, I _D =-1A, R _L =10Ω, V _{GEN} =-4.5V R _g =1Ω	-	11	20	nS
Turn-on Rise Time	t _r		-	35	60	
Turn-Off Delay Time	t _{d(off)}		-	30	50	
Turn-Off Fall Time	t _f		-	10	20	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I _S	T _C =25°C	-	-	-1.3	A
Pulse Diode Forward Current	I _{SM}	-	-	-	-10	A
Body Diode Voltage (1)	V _{SD}	I _S =-0.7A	-	-0.8	-1.2	V

(1) Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.

(2) Guaranteed by design, not subject to production testing.



TYPICAL PERFORMANCE CHARACTERISTICS

Fig 1. Output Characteristics

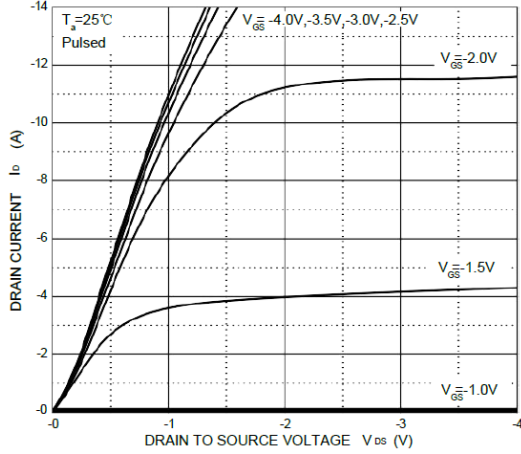


Fig 2. Transfer Characteristics

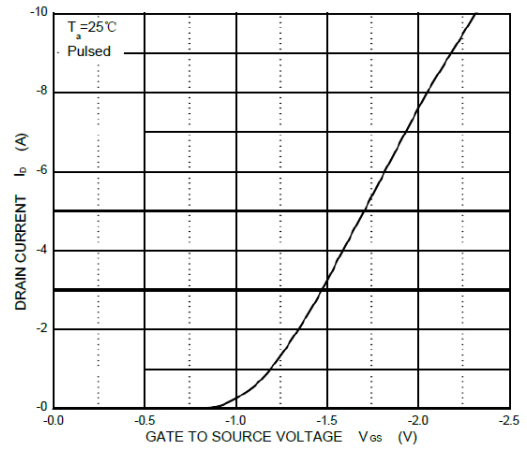


Fig 3. $R_{DS(ON)}$ vs. I_D

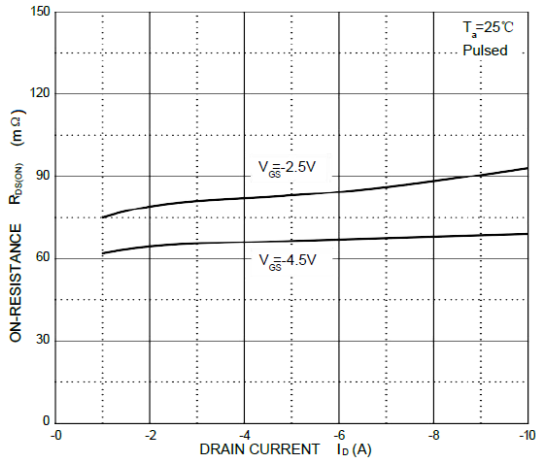


Fig 4. $R_{DS(ON)}$ vs. V_{GS}

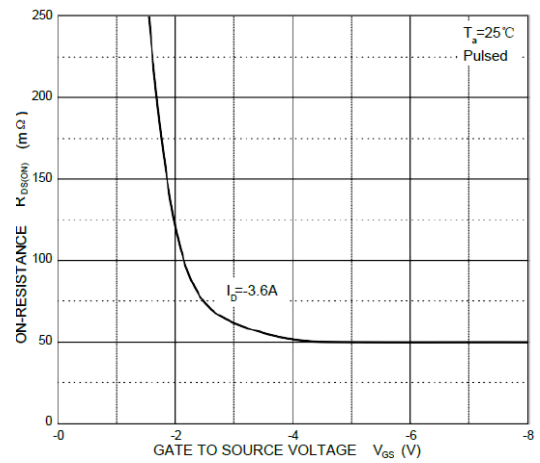
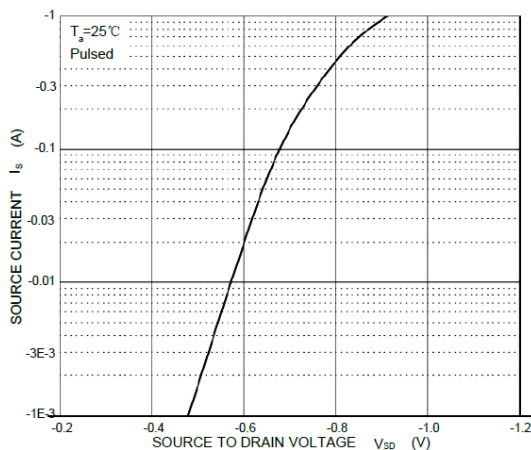


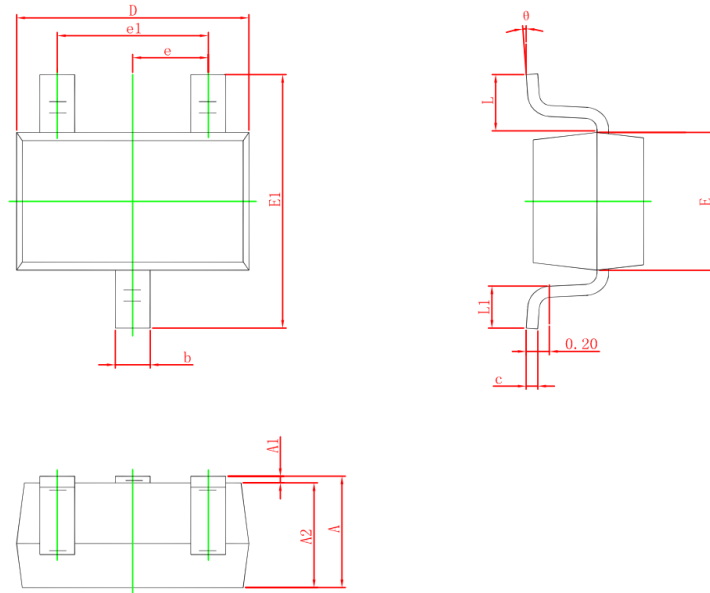
Fig 5. I_S vs. V_{SD}





PACKAGE INFORMATION

Dimension in SC70-3 (SOT-323) (Unit: mm)



SYMBOL	MILLIMETERS	
	Min.	Max.
A	0.900	1.100
A1	0.000	0.100
A2	0.900	1.000
b	0.200	0.400
c	0.080	0.150
D	2.000	2.200
E	1.150	1.350
E1	2.150	2.450
e	0.650 TYP.	
e1	1.200	1.400
L	0.525 REF.	
L1	0.260	0.460
θ	0°	8°



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